TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

# 2SA1832FT

## Audio frequency General Purpose Amplifier Applications

Unit: mm

• High voltage:  $V_{\rm CEO} = -50 \text{ V}$ 

• High current:  $I_C = -150 \text{ mA (max)}$ 

• High hFE: hFE = 120 to 400

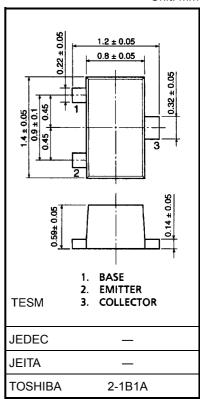
• Excellent hFE linearity

:  $h_{FE} (I_{C} = -0.1 \text{ mA})/h_{FE} (I_{C} = -2 \text{ mA}) = 0.95 \text{ (typ.)}$ 

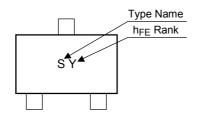
• Complementary to 2SC4738F

## **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ic	-150	mA
Base current	ΙΒ	-30	mW
Collector power dissipation	P <sub>C</sub>	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55 to 125	°C



#### Marking



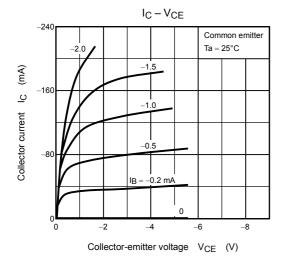
## **Electrical Characteristics (Ta = 25°C)**

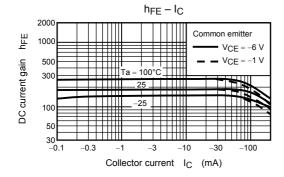
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-0.1	μА
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -5 \text{ V}, I_C = 0$		_	-0.1	μА
DC current gain	h <sub>FE</sub> (Note)	$V_{CE} = -6 \text{ V}, I_{B} = -2 \text{ mA}$	120	_	400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$	_	-0.1	-0.3	٧
Transition frequency	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}$	80	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	4	7	pF

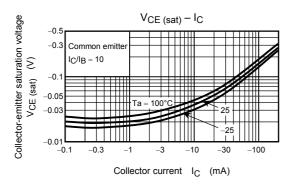
Note: hFE Classification

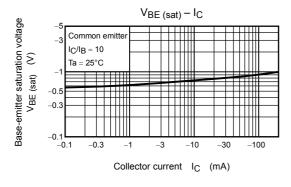
Y (Y): 120 to 140, GR (G): 200 to 400

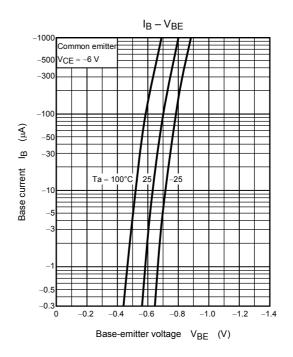
( ) Marking symbol

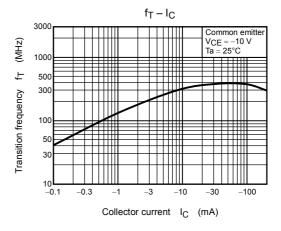


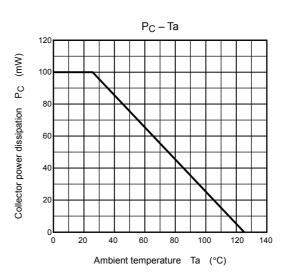












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